

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants: Ismail Kashkoush

Serial No.: 10/585,229

Filing Date: April 20, 2007

For: **SYSTEM AND METHOD FOR  
SELECTIVE ETCHING OF SILICON  
NITRIDE DURING SUBSTRATE  
PROCESSING**

Examiner: Lan Vinh

Art Unit: 1713

Confirmation No.: 9361

Attorney Docket No.: AKR-034-US

**RESPONSE TO RESTRICTION REQUIREMENT**

In response to the restriction requirement dated September 3, 2010, Applicant hereby elects without traverse Group I, which is drawn to a method for selective etching of silicon nitride during substrate processing and encompasses claims 1-12 and 22.

The Belles Group, P.C.

Date: October 4, 2010



By: Brian L. Belles, Esq. (Reg. No. 51,322)

For: ***The Belles Group, P.C.***  
1518 Walnut St.  
Suite 1706  
Philadelphia, PA 19102  
Office: 215-735-9302  
Cell: 215-749-2530  
Fax: 215-735-9305